

Type Designator: 2SB136

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation ( $P_c$ ): 0.15 W

Maximum Collector-Base Voltage [ $V_{cb}$ ]: 25 V

Maximum Collector-Emitter Voltage [ $V_{ce}$ ]: 25 V

Maximum Emitter-Base Voltage [ $V_{eb}$ ]: 12 V

Maximum Collector Current [ $I_c$  max]: 0.15 A

Max. Operating Junction Temperature ( $T_j$ ): 85 °C

Transition Frequency ( $f_t$ ): 0.3 MHz

Forward Current Transfer Ratio ( $h_{FE}$ ), MIN: 120

Noise Figure, dB: -

Package: TO1